

STPS61H100C

High voltage power Schottky rectifier

Datasheet - production data

Features

- High junction temperature capability
- Low leakage current
- Good trade off between leakage current and forward voltage drop
- Low thermal resistance
- High frequency operation

Description

Dual center tap Schottky rectifier suited for high frequency switch mode power supply.

Packaged in TO-247, this device is intended for use to enhance the reliability of the application.

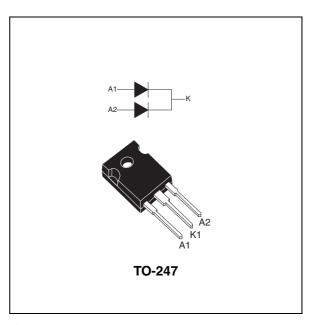


Table 1. Device summary

I _{F(AV)}	2 x 30 A
V_{RRM}	100 V
T _j (max)	175 °C
V _F (max)	0.67 V

Characteristics STPS61H100C

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage			100	V
I _{F(RMS)}	Forward rms current			80	Α
I _{F(AV)}	Average forward current	erage forward current $T_c = 150 ^{\circ}\text{C}$ Per diode $\delta = 0.5$ Per device		30 60	Α
I _{FSM}	Surge non repetitive forward current	rward current $t_p = 10 \text{ ms sinusoidal}$			Α
P _{ARM}	Repetitive peak avalanche power $t_p = 1 \mu s T_j = 25 ^{\circ}C$			26400	W
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Maximum operating junction temperature (1)			175	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs

^{1.} $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case	Per diode Total	0.9 0.6	°C/W
R _{th(c)}	Junction to case	Coupling	0.3	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta Tj(\text{diode 1}) = P(\text{diode1}) \; x \; R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \; x \; R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
ı (1)	$I_R^{(1)}$ Reverse leakage current $ T_j = 25 ^{\circ}\text{C} $ $T_j = 125 ^{\circ}\text{C} $ $V_R = V_{RRM}$		3	16	μΑ		
'R`		T _j = 125 °C	$v_R = v_{RRM}$		4	16	mA
	V _F ⁽¹⁾ Forward voltage drop	T _j = 25 °C	I _F = 30 A			0.79	
V (1)		T _j = 125 °C	I _F = 30 A		0.63	0.67	V
VF		T _j = 25 °C	I _F = 60 A			0.93	V
		T _j = 125 °C	I _F = 60 A		0.72	0.78	

^{1.} Pulse test: tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.56 \text{ x } I_{F(AV)} + 0.0036 I_{F}^{2}_{(RMS)}$$

STPS61H100C Characteristics

Figure 1. Conduction losses versus average Figure 2. Normalized avalanche power current (per diode) derating versus pulse duration

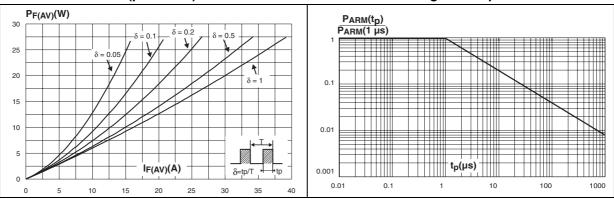


Figure 3. Normalized avalanche power derating versus junction temperature

Figure 4. Average forward current versus ambient temperature (δ = 0.5, per diode)

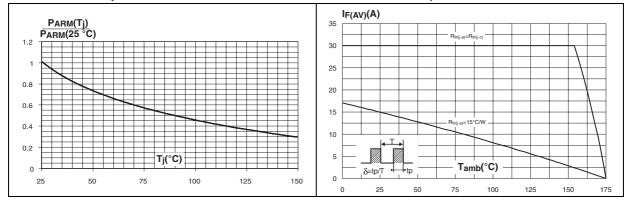
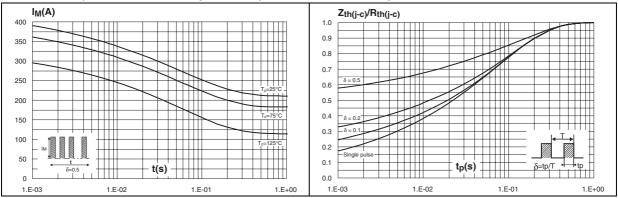


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 6. Relative variation of thermal impedance junction to case versus pulse duration



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Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)

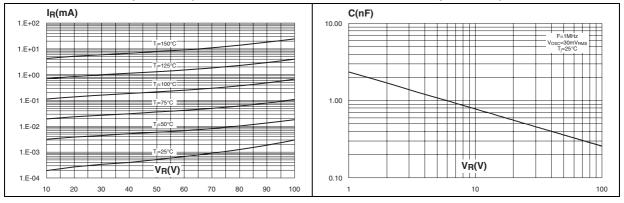
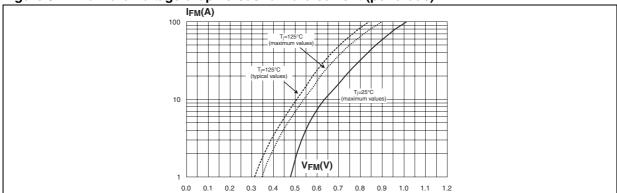


Figure 9. Forward voltage drop versus forward current (per diode)



2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Cooling method: Conduction
- Recommended torque value: 0.9 to 1.2 N⋅m

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Table 5. TO-247 dimensions

			Dimensions					
		Ref.	Mi	illimete	ers		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
	Α	4.85		5.15	0.191		0.203	
,		A1	2.20		2.60	0.086		0.102
	b	1.00		1.40	0.039		0.055	
E	E A Heat-sink plane ⊘P	b1	2.00		2.40	0.078		0.094
		b2	3.00		3.40	0.118		0.133
	С	0.40		0.80	0.015		0.031	
		D ⁽¹⁾	19.85		20.15	0.781		0.793
		Е	15.45		15.75	0.608		0.620
		е	5.30	5.45	5.60	0.209	0.215	0.220
2 1 3 b	BACKVIEW	L	14.20		14.80	0.559		0.582
e		L1	3.70		4.30	0.145		0.169
		L2	1	8.50 ty	p.	0	.728 typ	D.
		ØP ⁽²⁾	3.55		3.65	0.139		0.143
		ØR	4.50		5.50	0.177		0.217
		S	5.30	5.50	5.70	0.209	0.216	0.224

- 1. Dimension D plus gate protrusion does not exceed 20.5 mm
- 2. Resin thickness around the mounting hole is not less than 0.9 mm

Ordering information STPS61H100C

3 Ordering information

 Table 6.
 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS61H100CW	STPS61H100CW	TO-247	4.4 g	30	Tube

4 Revision history

Table 7. Document revision history

Date	Revision	Changes	
Oct-2003	1A	Previous version	
Sep-2006	2	Reformatted for internal distribution.	
12-Mar-2012	3	Updated package dimension nomenclature and illustration in Table 5. Dimensions of actual package remain unchanged.	

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